



**RB706F-40** SCHOTTKY BARRIER DIODE

**FEATURES**

Power dissipation

$P_D$ : 200 mW ( $T_{amb}=25^\circ C$ )

Collector current

$I_F$ : 30 mA

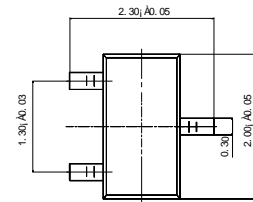
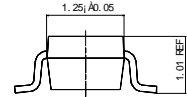
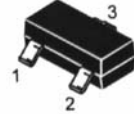
Collector-base voltage

$V_R$ : 40 V

Operating and storage junction temperature range

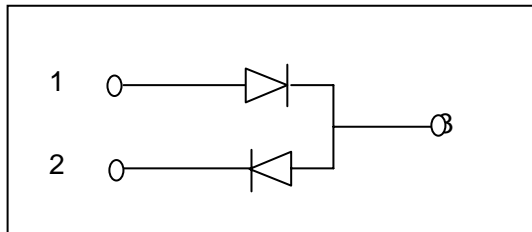
$T_J, T_{stg}$ :  $-55^\circ C$  to  $+150^\circ C$

**SOT-323**



Unit: mm

**CIRCUIT:**



**MARKING:** 3J

**ELECTRICAL CHARACTERISTICS ( $T_{amb}=25^\circ C$  unless otherwise specified)**

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	$I_R=100\mu A$	40		V
Reverse voltage leakage current	$I_R$	$V_R=10V$		1	$\mu A$
Forward voltage	$V_F$	$I_F=1mA$		0.37	V
Diode capacitance	$C_D$	$V_R=1V, f=1MHz$		5	pF